

74AUP1G06

SINGLE INVERTER WITH OPEN DRAIN OUTPUT

Description

The Advanced Ultra Low Power (AUP) CMOS logic family is designed for low power and extended battery life in portable applications.

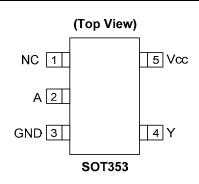
The 74AUP1G06 is a single inverter with an open drain output designed for operation over a power supply range of 0.8V to 3.6V. The device is fully specified for partial power down applications using I_{OFF} . The I_{OFF} circuitry disables the output preventing damaging current backflow when the device is powered down. The gate performs the positive Boolean function:

 $\mathsf{Y}=\overline{\mathsf{A}}$

Features

- Advanced Ultra Low Power (AUP) CMOS
- Supply Voltage Range from 0.8V to 3.6V
- ±4mA Output Drive at 3.0V
- Low Static power consumption
 - Icc < 0.9µA
- Low Dynamic Power Consumption
- C_{PD} = 6 pF (Typical at 3.6V)
- Schmitt Trigger Action at All Inputs Make the Circuit Tolerant for Slower Input Rise and Fall Time. The hysteresis is typically 250 mV at Vcc = 3.0V
- IOFF Supports Partial-Power-Down Mode Operation
- ESD Protection Exceeds JESD 22
 - 2000-V Human Body Model (A114-A)
 - Exceeds 1000-V Charged Device Model (C101C)
- Latch-Up Exceeds 100mA per JESD 78, Class II
- Range of Package Options SOT353, DFN1410, and DFN1010
- Leadless packages per JESD30E
 - DFN1010 denoted as X2-DFN1010-6
 - DFN1014 denoted as X2-DFN1014-6
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Pin Assignments





(Гор	View	V)
NC	1	6	Vcc
			Vcc NC
GND	3	[4	Y
I	DFN	1010)

Applications

- Suited for battery and low power needs
 - Wide array of products such as:
 - Tablets, E-readers
 - Cell Phones, Personal Navigation / GPS
 - MP3 players ,Cameras, Video Recorders
 - PCs ultrabooks, notebooks, netbooks,
 - Computer peripherals, hard drives, CD/DVD ROM
 - TV, DVD, DVR, set top box

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

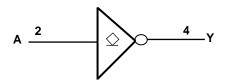
Click here for ordering information, located at the end of datasheet



Pin Descriptions

Pin Name	Function
NC	No Connection
A	Data Input
GND	Ground
Y	Data Output
V _{CC}	Supply Voltage

Logic Diagram



Function Table

Inputs	Output
Α	Y
Н	L
L	Z



Absolute Maximum Ratings (Note 4) (@T_A = +25°C, unless otherwise specified.)

Symbol	Parameter	Rating	Unit				
ESD HBM	Human Body Model ESD Protection	2	KV				
ESD CDM	Charged Device Model ESD Protection	1 K					
V _{CC}	Supply Voltage Range	-0.5 to +4.6	V				
VI	Input Voltage Range	-0.5 to +4.6	V				
Vo	Voltage applied to output in high or low state	-0.5 to V _{CC} +0.5					
I _{IK}	Input Clamp Current VI < 0	50	mA				
loк	Output Clamp Current ($V_0 < 0$)	50					
lo	Continuous output Current (V _O = 0 to V _{CC})	±20	mA				
I _{CC}	Continuous Current Through V _{CC}	50	mA				
I _{GND}	Continuous Current Through GND	-50	mA				
TJ	Operating Junction Temperature	-40 to +150	°C				
T _{STG}	Storage Temperature	-65 to +150	°C				

Note: 4. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

Recommended Operating Conditions (Note 5) (@T_A = +25°C, unless otherwise specified.)

Symbol	Pa	rameter	Min	Max	Unit
V _{CC}	Operating Voltage		0.8	3.6	V
VI	Input Voltage		0	3.6	V
Vo	Output Voltage		0	Vcc	V
		$V_{CC} = 0.8V$		20	uA
		$V_{CC} = 1.1V$		1.1	
	Low-Level Output Current	$V_{CC} = 1.4V$		1.7	
IOL		V _{CC} = 1.65V		1.9	mA
		$V_{CC} = 2.3V$		3.1	
		$V_{CC} = 3.0V$		4	
Δt/ΔV	Input Transition Rise or Fall Rate	$V_{CC} = 0.8V$ to 3.6V		200	ns/V
TA	Operating Free-Air Temperature		-40	125	°C

Note: 5. Unused inputs should be held at V_{CC} or Ground.



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Sympol	Parameter	Test Conditions	V	T _A = -	+25°C	T _A = -40°0	C to +85°C	Unit
Symbol	Parameter	Test Conditions	Vcc	Min	Max	Min	Max	Unit
			0.8V to 1.65V	0.80 X V _{CC}		0.80 X V _{CC}		
V	High-Level Input Voltage		1.65V to 1.95V	0.65 X V _{CC}		0.65 X V _{CC}		V
VIH	nigh-Level input voltage		2.3V to 2.7V	1.6		1.6		v
			3.0V to 3.6V	2.0		2.0		
			0.8V to 1.65V		0.30 X V _{CC}		0.30 X V _{CC}	
VIL	Low-Level Input Voltage		1.65V to 1.95V		0.35 X V _{CC}		0.35 X V _{CC}	V
۷IL			2.3V to 2.7V		0.7		0.7	v
			3.0V to 3.6V		0.9		0.9	
		I _{OL} = 20μA	0.8V to 3.6V		0.1		0.1	
		I _{OL} = 1.1mA	1.1V		0.3 X V _{CC}		0.3 X V _{CC}	V
		I _{OL} = 1.7mA	1.4V		0.31		0.37	
.,		I _{OL} = 1.9mA	1.65V		0.31		0.35	
V _{OL}	High-Level Input Voltage	I _{OL} = 2.3mA	0.01/		0.31		0.33	
		I _{OL} = 3.1mA	2.3V		0.44		0.45	
		$I_{OL} = 2.7 \text{mA}$	a) /		0.31		0.33	
		$I_{OL} = 4mA$	3V		0.44		0.45	
I _I	Input Current	A or B Input V _I = GND to 3.6V	0V to 3.6V		± 0.1		± 0.5	μA
I _{OFF}	Power Down Leakage Current	$V_1 \text{ or } V_0 = 0V \text{ to } 3.6V$	0V		± 0.2		± 0.5	μA
I _{OZ}	Z State Leakage Current	$V_0 = 3.6V$ $V_i = 3.6V$	3.6V		± 0.2		± 0.5	μA
ΔI_{OFF}	Delta Power Down Leakage Current	$V_1 \text{ or } V_0 = 0V \text{ to } 3.6V$	0V to 0.2V		0.2		0.6	μA
Icc	Supply Current	$V_I = GND \text{ or } V_{CC},$ $I_O = 0$	0.8Vto 3.6V		0.5		0.9	μA
Δl _{CC}	Additional Supply Current	Input at V _{CC} -0.6V	3.3V		40		50	μA



Electrical Characteristics (cont.) (@T_A = +25°C, unless otherwise specified.)

Symbol	Parameter	Test Conditions	V	T _A = -40°C	to +125°C	Unit
Symbol	Parameter	Test Conditions	V _{cc}	Min	Max	Unit
			0V to 1.65V	0.80 X V _{CC}		
Vін	High-Level Input		1.65V to 1.95V	0.70 X V _{CC}		v
VIH	Voltage		2.3V to 2.7 V	1.6		v
			3.0 V to 3.6V	2.0		
			0.8V to 1.65V		0.25X V _{CC}	
VIL	Low-Level Input Voltage		1.65V to 1.95V		0.35 X V _{CC}	V
VIL			2.3V to 2.7V		0.7	v
			3.0V to 3.6V		0.9	
		$I_{OL} = 20\mu A$	0.8V to 3.6V		0.11	
	High-Level Input	$I_{OL} = 1.1 \text{mA}$	1.1V		0.3 X V _{CC}	
		$I_{OL} = 1.7 \text{mA}$	1.4V		0.41	
N/		I _{OL} = 1.9mA	1.65V		0.39	v
V _{OL}	Voltage	I _{OL} = 2.3mA	2.3V		0.36	v
		I _{OL} = 3.1mA	2.30		0.50	_
		$I_{OL} = 2.7 \text{mA}$	0) (0.36	
		$I_{OL} = 4mA$	3V		0.50	
h	Input Current	A or B Input V _I = GND to $3.6V$	0V to 3.6V		± 0.75	μA
I _{OFF}	Power Down Leakage Current	V_{I} or $V_{O} = 0V$ to 3.6V	0V		± 3.5	μA
I _{OZ}	Z State Leakage Current	$V_{O} = 3.6V$ $V_{i} = 3.6V$	3.6V		± 1.5	μA
ΔI_{OFF}	Delta Power Down Leakage Current	V_{I} or $V_{O} = 0V$ to 3.6V	0V to 0.2V		± 2.5	μA
Icc	Supply Current	$V_I = GND \text{ or } V_{CC}, I_O = 0$	0.8V to 3.6V		3.0	μA
ΔI _{CC}	Additional Supply Current	Input at V _{CC} -0.6V	3.3V		75	μA



Switching Characteristics

C_L = 5pF see Figure 1

Parameter From		то	то		T _A = +25°C		T _A = -40°C to +85°C		T _A = -40°C to +125°C		Unit
rarameter	Input	OUTPUT	Vcc	Min	Тур	Max	Min	Max	Min	Max	Onit
	t _{pd} A Y		0.8V		12.8						
			1.2V ± 0.1V	2.0	4.3	9.9	2	10.9	2	12	ns
4		V	1.5V ± 0.1V	1.5	3.1	6.1	1.5	7.1	1.5	7.8	
τ _{pd}		r	1.8V ± 0.15V	1.2	2.8	4.7	1.2	5.7	1.2	6.3	
			2.5V ± 0.2V	1	2.2	3.2	1	3.9	1	4.3	
			3.3V ± 0.3V	0.8	2.2	3.3	0.8	3.6	0.8	4	

$C_L = 10 pF$ see Figure 1

Parameter	From	то	Vee	T _A = +25°C		T _A = -40°C to +85°C		T _A = -40°C to +125°C		Unit	
Falameter	Input			Min	Тур	Max	Min	Max	Min	Max	Onit
	t _{pd} A Y		0.8V		15.8						
		Y	1.2V ± 0.1V	2.5	5.4	11.2	2.5	13.2	2.5	15	ns
			1.5V ± 0.1V	2	3.9	7	2	8.5	2	9.4	
τ _{pd}			1.8V ± 0.15V	1.7	3.6	5.4	1.7	6.7	1.7	7.4	
			2.5V ± 0.2V	1.4	2.9	3.8	1.4	4.5	1.4	5	
			3.3V ± 0.3V	1.2	3.2	4.6	1.2	4.9	1.2	5.4	

$C_L = 15 pF$ see Figure 1

Parameter	From	то	V	Т	T _A = +25°C		T _A = -40°C to +85°C		T _A = -40°C to +125°C		Unit
Farameter	Input	OUTPUT	Vcc	Min	Тур	Max	Min	Max	Min	Max	Unit
		0.8V		18.8							
		1.2V ± 0.1V	2.9	6.4	12.2	2.9	15.2	2.9	17		
	٨	Ň	1.5V ± 0.1V	2.3	4.6	7.7	2.3	9.4	2.3	10	
t _{pd} A	ř	1.8V ± 0.15V	2.1	4.5	6.6	2.1	7.3	2.1	8.1	ns	
		2.5V ± 0.2V	1.7	3.5	4.6	1.7	5.1	1.7	5.7		
			3.3V ± 0.3V	1.5	4	6	1.5	6.5	1.5	7.2	

$C_L = 30 pF$ see Figure 1

Parameter	From	то	N	Т	T _A = +25°C		T _A = -40°C to +85°C		T _A = -40°C to +125°C		Unit
Farameter	Input	OUTPUT	PUT V _{CC} M		Тур	Max	Min	Max	Min	Max	Onit
			0.8 V		27.8						
		1.2V ± 0.1V	3.9	9.3	16.5	3.9	19.3	3.9	21.3		
	۸	Ň	1.5V ± 0.1V	3.2	6.8	10.1	3.2	12	3.2	13.2	ns
t _{pd}	ipd A	T	1.8 V ± 0.15V	2.9	6.8	10.7	2.9	11	2.9	12.1	
		2.5V ± 0.2V	2.5	5.3	7.2	2.5	7.8	2.5	8.6		
			3.3V ± 0.3V	2.3	6.5	10.5	2.3	10.8	2.3	11.9	

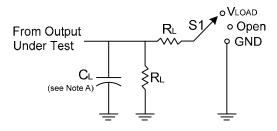


Operating and Package Characteristics (@T_A = +25°C, unless otherwise specified.)

	Parameter	Test Conditions		Vcc	Тур	Unit
				0.8V	2.6	
				1.2V ± 0.1V	2.8	
0	Power Dissipation	f = 1MHz		1.5V ± 0.1V	2.9	
C _{pd}	Capacitance	No Load		1.8V ± 0.15V	3.1	pF
				2.5V ± 0.2V	3.6	
			3.3V ± 0.3V	4.2		
Ci	Input Capacitance	V _i = V _{CC} o	r GND	0V or 3.3V	1.5	pF
		SOT353			371	
θ _{JA}	Thermal Resistance Junction-to-Ambient	X2-DFN1410-6	I1410-6 (Note 6)		430	°C/W
	Junction-to-Ambient	X2-DFN1010-6			445	
	T ID 14	SOT353			143	
θ_{JC}	Thermal Resistance Junction-to-Case	X2-DFN1410-6	(Note 6		190	°C/W
	Junction-to-Case	X2-DFN1010-6			250	

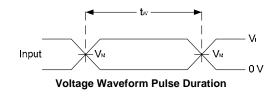
Notes: 6. Test condition for SOT353, X2-DFN1410-6, and X2-DFN1010-6 devices mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

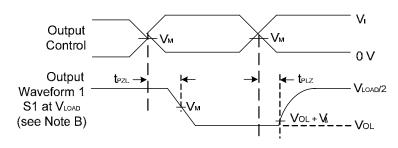
Parameter Measurement Information



TEST	S 1	RL
t _{PLZ} /t _{PZL}	Vload	5ΚΩ

V	In	puts	V	V	•	VA
V _{cc}	VI	t _r /t _f	V _M	VLOAD	CL	VΔ
0.8V	V _{CC}	≤3ns	V _{CC} /2	2 X V _{CC}	5, 10, 15, 30pF	0.1V
1.2V±0.1V	V _{CC}	≤3ns	V _{CC} /2	2 X V _{CC}	5, 10, 15, 30pF	0.1V
1.5V±0.1V	Vcc	≤3ns	V _{CC} /2	2 X V _{CC}	5, 10, 15, 30pF	0.1V
1.8V±0.15V	V _{CC}	≤3ns	V _{CC} /2	2 X V _{CC}	5, 10, 15, 30pF	0.15V
2.5V±0.2V	V _{CC}	≤3ns	V _{CC} /2	2 X V _{CC}	5, 10, 15, 30pF	0.15V
3.3V±0.3V	Vcc	≤3ns	V _{CC} /2	2 X V _{CC}	5, 10, 15, 30pF	0.3V





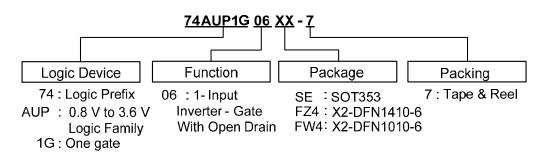
Voltage Waveform Enable and Disable Times Low and High Level Enabling

Figure 1. Load Circuit and Voltage Waveforms

- Notes: A. Includes test lead and test apparatus capacitance.
 - B. All pulses are supplied at pulse repetition rate \leq 10 MHz.
 - C. Inputs are measured separately one transition per measurement.
 - D. For the open drain device the specified propagation delay tPD is the same as tPLZ and tPZL.



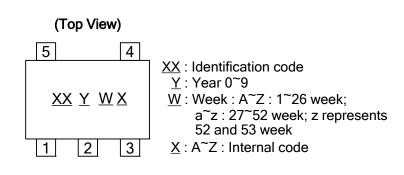
Ordering Information



	Part Number	Package Code Packaging	7" Tape and Reel		
	Part Number		Fackage Code Fackaging	Quantity	Part Number Suffix
Pb,	74AUP1G06SE-7	SE	SOT353	3000/Tape & Reel	-7
Pb,	74AUP1G06FZ4-7	FZ4	X2-DFN1410-6	5000/Tape & Reel	-7
Pb,	74AUP1G06FW4-7	FW4	X2-DFN1010-6	5000/Tape & Reel	-7

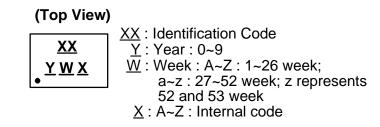
Marking Information

(1) SOT353



Part Number	Package	Identification Code
74AUP1G06SE	SOT353	XM

(2) X2-DFN1410-6 and X2-DFN1010-6



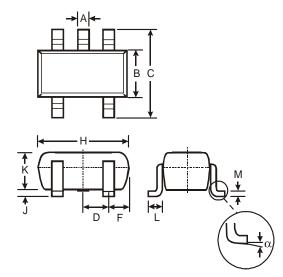
Part Number	Package	Identification Code
74AUP1G06FZ4	X2-DFN1410-6	XM
74AUP1G06FW4	X2-DFN1010-6	XM



Package Outline Dimensions (All dimensions in mm.)

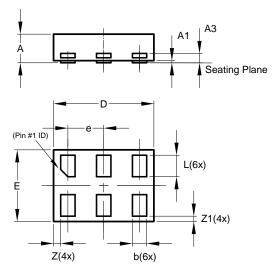
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.

(1) SOT353



	SOT353				
Dim	Min	Max	Тур		
Α	0.10	0.30	0.25		
В	1.15	1.35	1.30		
С	2.00	2.20	2.10		
D	0	.65 Typ)		
F	0.40	0.45	0.425		
Н	1.80	2.20	2.15		
J	0	0.10	0.05		
Κ	0.90	1.00	1.00		
L	0.25	0.40	0.30		
Μ	0.10	0.22	0.11		
α	0°	8°	-		
All	All Dimensions in mm				

(2) X2-DFN1410-6



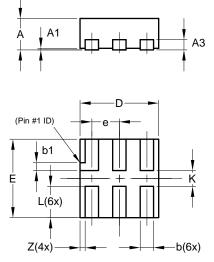
X2-DFN1410-6				
Dim	Min	Max	Тур	
Α		0.40	0.39	
A1	0.00	0.05	0.02	
A3			0.13	
b	0.15	0.25	0.20	
D	1.35	1.45	1.40	
ш	0.95	1.05	1.00	
е	_		0.50	
L	0.25	0.35	0.30	
Z			0.10	
Z1	0.045	0.105	0.075	
All Dimensions in mm				



Package Outline Dimensions (cont.) (All dimensions in mm.)

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.

(3) X2-DFN1010-6

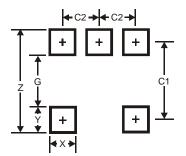


	X2-DFN1010-6				
Dim	Min	Max	Тур		
Α		0.40	0.39		
A1	0.00	0.05	0.02		
A3			0.13		
b	0.14	0.20	0.17		
b1	0.05	0.15	0.10		
D	0.95	1.05	1.00		
E	0.95	1.05	1.00		
е			0.35		
L	0.35	0.45	0.40		
K	0.15				
Z		_	0.065		
All [All Dimensions in mm				

Suggested Pad Layout

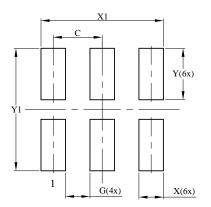
Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version

(1) SOT353



Dimensions	Value (in mm)
Z	2.5
G	1.3
Х	0.42
Y	0.6
C1	1.9
C2	0.65

(2) X2-DFN1410-6



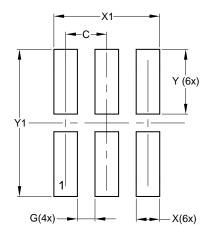
Dimensions	Value (in mm)
С	0.500
G	0.250
Х	0.250
X1	1.250
Y	0.525
Y1	1.250



Suggested Pad Layout (cont.)

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

(3) X2-DFN1010-6



Dimensions	Value (in mm)
С	0.350
G	0.150
Х	0.200
X1	0.900
Y	0.550
Y1	1.250

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 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

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